

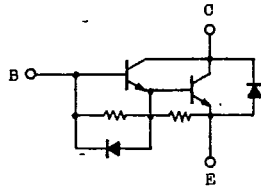
9097250 TOSHIBA (DISCRETE/OPTO)

90D 16279 DT-33-35

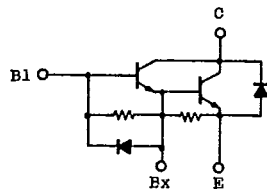


SEMICONDUCTOR
TECHNICAL DATA

MG200H1AL2
MG200H1FL1A

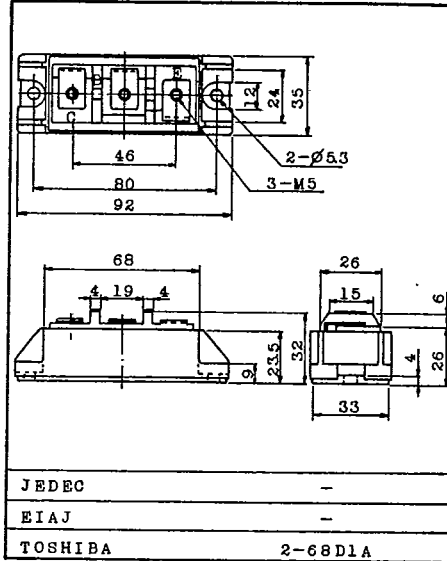


MG200H1AL2



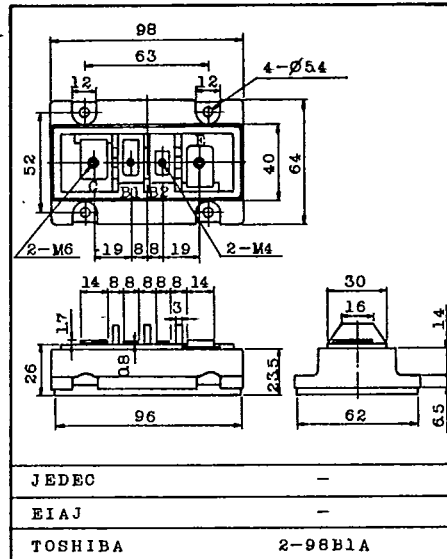
MG200H1FL1

Unit in mm



Weight : 210g

Unit in mm



Weight : 420g

TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)

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DT-33-35



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MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB10}	600	V
Collector-Emitter Voltage	V _{CEO}	600	V
Collector-Emitter Sustaining Voltage	V _{CEO(SUS)}	550	V
Emitter-Base Voltage	V _{EB10}	6	V
Collector Current	DC	I _C	200
	1ms	I _C	400
	DC	-I _C	200
Base Current	I _{B1}	8	A
Collector Power Dissipation (Tc=25°C)	P _C	800	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-40~125	°C
Isolation Voltage	V _{isol}	2500 (AC 1 Minute)	V
Screw Torque (Terminal M4/M6/Mounting)	-	20/30/30	kg·cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I _{CB10}	V _{CB1} =600V, I _E =0	-	-	2.0	mA	
Emitter Cut-off Current	I _{EB10}	V _{EB1} =6V, I _C =0	-	-	400	mA	
Collector-Emitter Sustaining Voltage	V _{CEO(SUS)}	I _C =0.5A, L=40mH	550	-	-	V	
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =200A	80	-	-		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =200A, I _{B1} =6A	-	-	2.0	V	
Base-Emitter Saturation Voltage	V _{BE1(sat)}		-	-	2.7	V	
Emitter-Collector Voltage	V _{ECO}	I _E =200A, I _{B1} =0	-	-	1.5	V	
Reverse Recovery Time	t _{rr}	-I _C =200A, V _{EB1} =3V V _{CE} =300V	-	-	2.0	μs	
Collector Output Capacitance	C _{ob1}	V _{CB1} =50V, I _E =0 f=1MHz	-	1670	-	pF	
Switching Time	Turn-on Time	t _{on}			-	2.0	μs
	Storage Time	t _{stg}			-	12	
	Fall Time	t _f	I _{B1} =-I _{B2} =6A DUTY CYCLE=0.5%		-	4.0	
Thermal Resistance (Junction to Case)	R _{th(j-c)}	Transistor	-	-	0.156	°C/W	
		Diode	-	-	0.65		

TOSHIBA CORPORATION

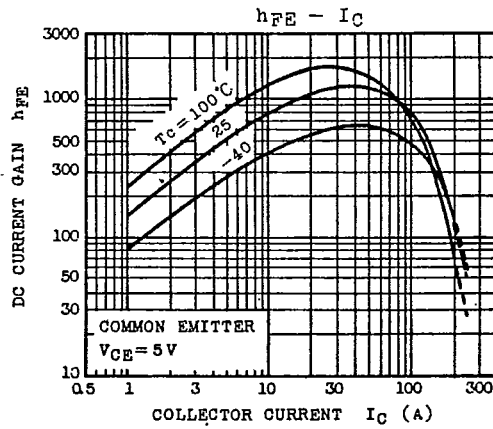
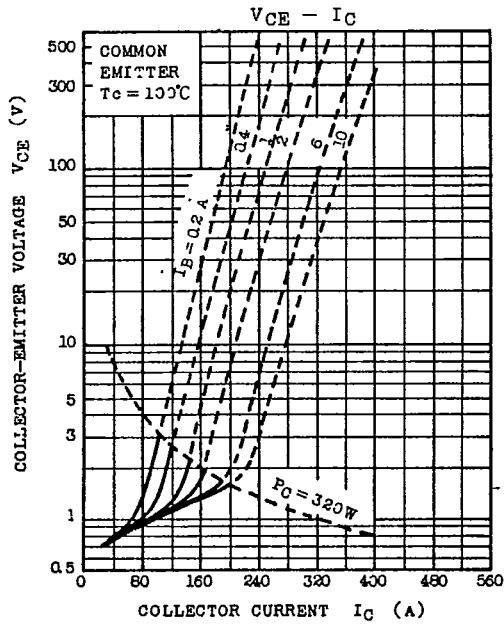
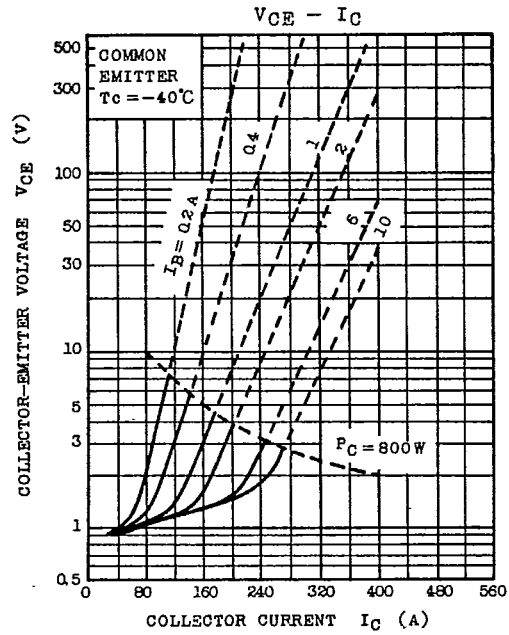
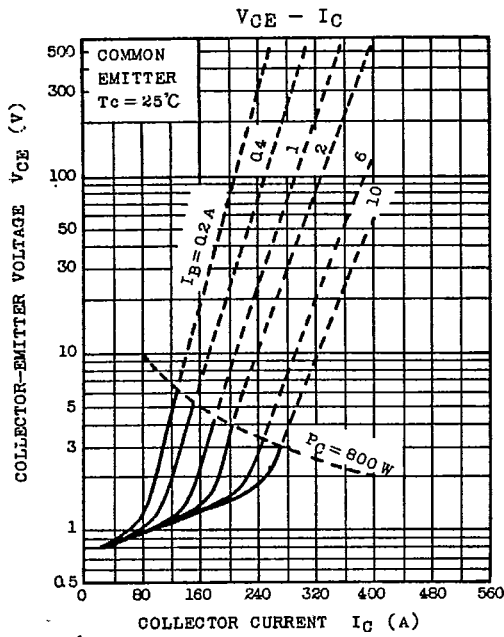
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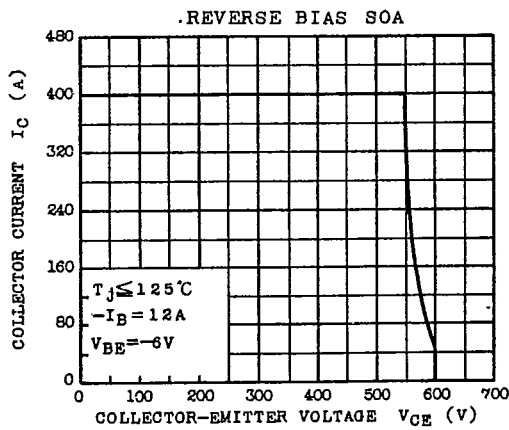
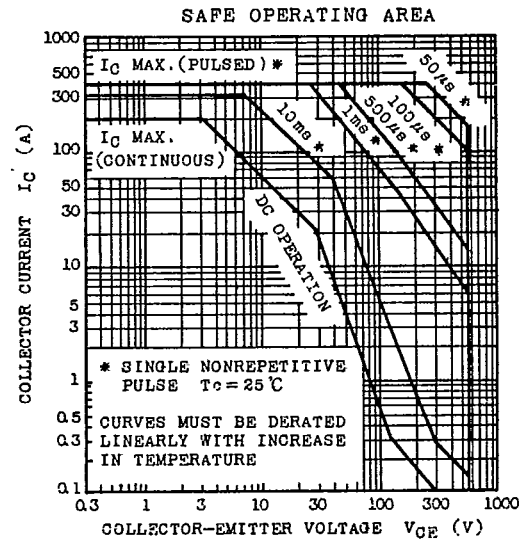
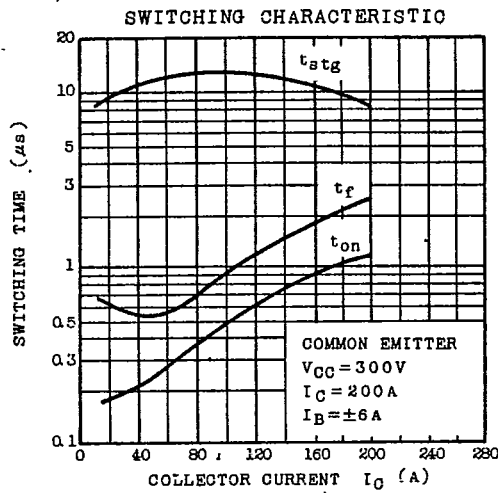
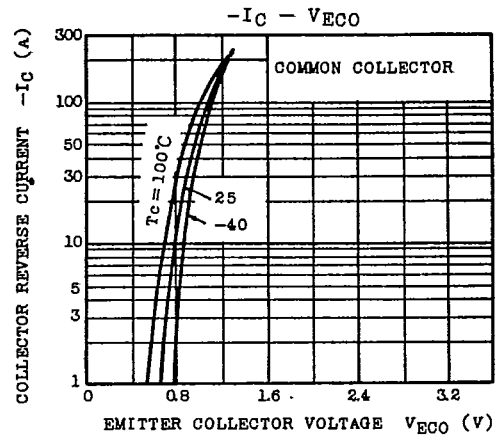
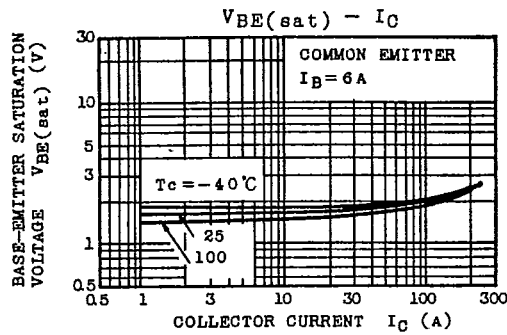
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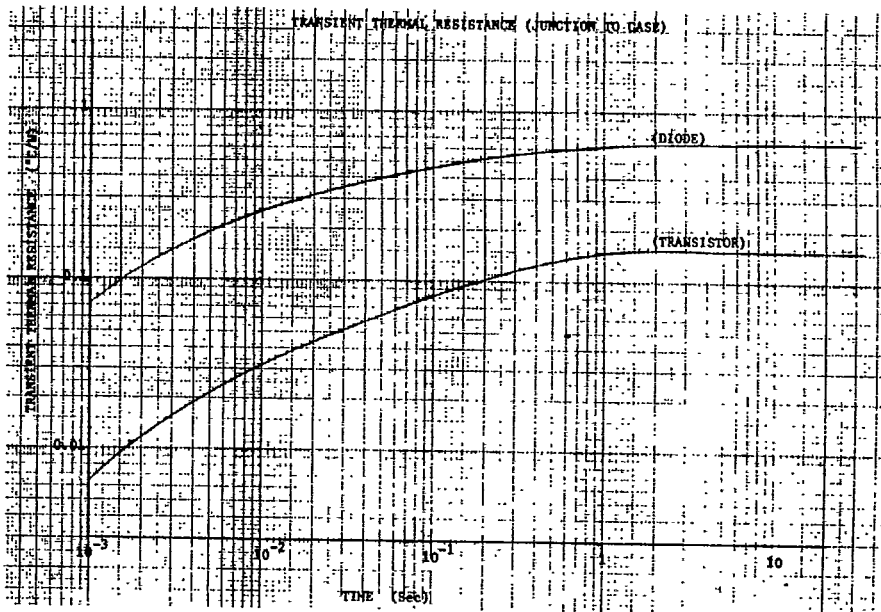
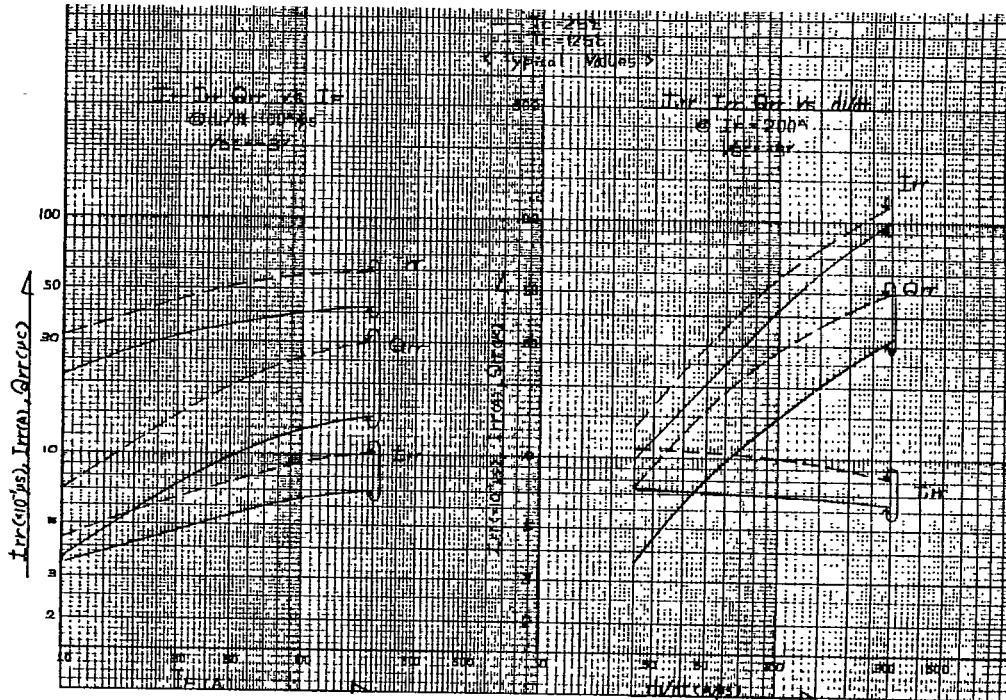


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